

n-channel JFET

designed for . . .

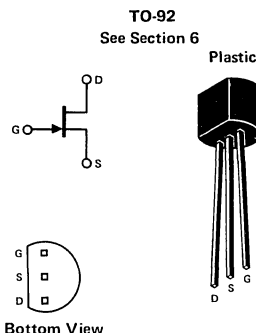
■ Low and Medium Frequency Amplifiers

BENEFITS

- Low Cost

ABSOLUTE MAXIMUM RATINGS (25°C)

Gate-Drain or Gate-Source Voltage -25V
 Gate Current (FWD) 10 mA
 Total Device Dissipation at 25°C Ambient
 (Derate 3.27 mW/°C). 360 mW
 Operating Temperature Range. -55 to 135°C
 Storage Temperature Range. -55 to 150°C
 Lead Temperature Range
 (1/16" from case for 10 seconds) 300°C



*ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

Characteristic			Min	Max	Unit	Test Conditions				
1	S T A T I C	I _{GSS}	Gate Reverse Current		−10	nA	V _{GS} = −15 V, V _{DS} = 0			
2					−0.6	μA		T _A = 85°C		
3		BV _{GSS}	Gate-Source Breakdown Voltage	−25			I _G = −10 μA, V _{DS} = 0			
4		V _{GS(off)}	Gate-Source Cutoff Voltage	−0.4	−8.0	V	V _{DS} = 15 V, I _D = 1 μA			
5		V _{GS}	Gate-Source Voltage		−7.5		V _{DS} = 15 V, I _D = 100 μA			
6	I _{DSS}	Saturation Drain Current	1.0	40	mA	V _{DS} = 15 V, V _{GS} = 0				
7	r _{ds(on)}	Drain-Source ON Resistance		500	Ω	V _{GS} = 0, I _D = 0				
8	D Y N A M I C	g _{fs}	Common-Source Forward Transconductance	2000	9000	μmho	V _{DS} = 15 V, V _{GS} = 0	f = 1 kHz		
9		g _{os}	Common-Source Output Conductance		200					
10		g _{fs}	Common-Source Forward Transconductance	1800					f = 1 MHz	
11		C _{iss}	Common-Source Input Capacitance		20	pF				
12		C _{rss}	Common-Source Reverse Transfer Capacitance		5.0					
13	NF	Common-Source Spot Noise Figure		3.0	dB	V _{DS} = 15 V, I _D = 1 mA	R _G = 150k Ω	f = 1 kHz		
14	e _N	Equivalent Short Circuit Input Noise Voltage		50	$\frac{nV}{\sqrt{Hz}}$			NBW = 150 Hz		

*JEDEC registered data